

Dual Precision Retriggerable/Resettable Monostable Multivibrator

MC14538B

The MC14538B is a dual, retriggerable, resettable monostable multivibrator. It may be triggered from either edge of an input pulse, and produces an accurate output pulse over a wide range of widths, the duration and accuracy of which are determined by the external timing components, C_X and R_X . Output Pulse Width $T = R_X \cdot C_X$ (secs)

 $R_X = \Omega$ $C_X = Farads$

Features

- Unlimited Rise and Fall Time Allowed on the A Trigger Input
- Pulse Width Range = 10 μs to 10 s
- Latched Trigger Inputs
- Separate Latched Reset Inputs
- 3.0 Vdc to 18 Vdc Operational Limits
- Triggerable from Positive (A Input) or Negative–Going Edge (B–Input)
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load Over the Rated Temperature Range
- Pin-for-pin Compatible with MC14528B and CD4528B (CD4098)
- $\bullet\,$ Use the MC54/74HC4538A for Pulse Widths Less Than 10 μs with Supplies Up to 6 V
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V _{in} , V _{out}	Input or Output Voltage Range (DC or Transient)	-0.5 to V _{DD} + 0.5	V
I _{in} , I _{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P _D	Power Dissipation, per Package (Note 1)	500	mW
T _A	Operating Temperature Range	-55 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8-Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Packages: -7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}.$

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



SOIC-16 D SUFFIX CASE 751B

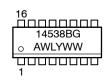


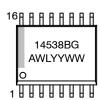
SOIC-16WB DW SUFFIX CASE 751G



TSSOP-16 DT SUFFIX CASE 948F

MARKING DIAGRAMS





SOIC-16

SOIC-16WB



TSSOP-16

A = Assembly Location

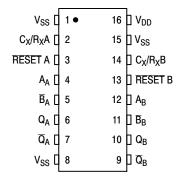
WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or = Pb-Free Indicator

(Note: Microdot may be in either location)

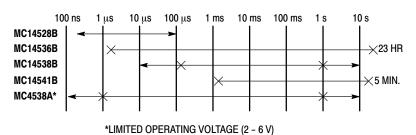
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

PIN ASSIGNMENT



ONE-SHOT SELECTION GUIDE

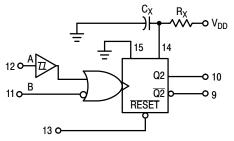


TOTAL OUTPUT PULSE WIDTH RANGE ←

RECOMMENDED PULSE WIDTH RANGE X

$\begin{array}{c|c} C_X & R_X \\ \hline & & & & \\ \hline & & & \\ \hline & & & &$

BLOCK DIAGRAM



 R_X AND C_X ARE EXTERNAL COMPONENTS. V_{DD} = PIN 16 V_{SS} = PIN 8, PIN 1, PIN 15

ORDERING INFORMATION

Device	Package	Shipping [†]
MC14538BDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC14538BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14538BDR2G*	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
MC14538BDTR2G	TSSOP-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14538BDTR2G*	TSSOP-16 (Pb-Free)	2500 Units / Tape & Reel
MC14538BDWG	SOIC-16 WB (Pb-Free)	47 Units / Rail
NLV14538BDWG*	SOIC-16 WB (Pb-Free)	47 Units / Rail
MC14538BDWR2G	SOIC-16 WB (Pb-Free)	1000 Units / Tape & Reel
NLV14538BDWR2G*	SOIC-16 WB (Pb-Free)	1000 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

		\ \ \	- 5	5°C		25°C		125	5°C	
Characteristic	Symbol	V _{DD} Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage "0" Level V _{in} = V _{DD} or 0	V _{OL}	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
V _{in} = 0 or V _{DD} "1" Level	V _{OH}	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage "0" Level (V _O = 4.5 or 0.5 Vdc) (V _O = 9.0 or 1.0 Vdc) (V _O = 13.5 or 1.5 Vdc)	V _{IL}	5.0 10 15	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	V _{IH}	5.0 10 15	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	- - -	Vdc
	Іон	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2	- - -	-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8	- - -	-1.7 -0.36 -0.9 -2.4	- - -	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ Sink $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	l _{OL}	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4	- - -	mAdc
Input Current, Pin 2 or 14	l _{in}	15	-	±0.05	-	±0.00001	±0.05	-	±0.5	μAdc
Input Current, Other Inputs	l _{in}	15	-	±0.1	-	±0.00001	±0.1	-	±1.0	μAdc
Input Capacitance, Pin 2 or 14	C _{in}	-	-	-	-	25	-	-	-	pF
Input Capacitance, Other Inputs (V _{in} = 0)	C _{in}	-	-	-	-	5.0	7.5	-	-	pF
Quiescent Current (Per Package) Q = Low, Q = High	I _{DD}	5.0 10 15	- - -	5.0 10 20	- - -	0.005 0.010 0.015	5.0 10 20	- - -	150 300 600	μAdc
Quiescent Current, Active State (Both) (Per Package) Q = High, Q = Low	I _{DD}	5.0 10 15	- - -	2.0 2.0 2.0	- - -	0.04 0.08 0.13	0.20 0.45 0.70	- - -	2.0 2.0 2.0	mAdc
Total Supply Current at an external load capacitance (C _L) and at external timing network (R _X , C _X) (Note 3)	I _T	5.0 10		$I_T = (8.0 \text{ s})$ $I_T = (1.25 \text{ where:})$	x 10 ^{–2}) R 5 x 10 ^{–1}) I I _T in μA (σ C _X in μF,	$_{c}^{\prime}$ C _X f + 4C _X f - $_{c}$ C _X f + 9C _X f R _X C _X f + 12C cone monosta C _L in pF, R _X the input free	+ 2 x 10 ⁻⁵ xf + 3 x 10 ble switch in k ohms	⁵ C _L f 0 ^{–5} C _L f ning only),		μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

OPERATING CONDITIONS

External Timing Resistance	R_X	-	5.0	-	(Note 4)	kΩ
External Timing Capacitance	C _X	_	0	-	No Limit (Note 5)	μF

^{4.} The maximum usable resistance R_X is a function of the leakage of the capacitor C_X , leakage of the MC14538B, and leakage due to board layout and surface resistance. Susceptibility to externally induced noise signals may occur for $R_X > 1$ M Ω .

^{2.} Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

^{3.} The formulas given are for the typical characteristics only at 25°C.

^{5.} If $C_X > 15 \mu F$, use discharge protection diode per Fig. 11.

SWITCHING CHARACTERISTICS (Note 6) ($C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$)

		.,				
Characteristic	Symbol	V _{DD} Vdc	Min	Typ (Note 7)	Max	Unit
Output Rise Time $t_{TLH} = (1.35 \text{ ns/pF}) C_L + 33 \text{ ns} $ $t_{TLH} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$	t _{TLH}	5.0 10		100 50	200 100	ns
$t_{TLH} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$		15	-	40	80	
Output Fall Time $t_{THL} = (1.35 \text{ ns/pF}) C_L + 33 \text{ ns}$ $t_{THL} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{THL} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$	t _{THL}	5.0 10 15	- - -	100 50 40	200 100 80	ns
Propagation Delay Time A or B to Q or \overline{Q} t_{PLH} , t_{PHL} = (0.90 ns/pF) C_L + 255 ns	t _{PLH} , t _{PHL}	5.0	-	300	600	ns
t_{PLH} , t_{PHL} = (0.36 ns/pF) C_L + 132 ns t_{PLH} , t_{PHL} = (0.26 ns/pF) C_L + 87 ns		10 15	_ _	150 100	300 220	
$\label{eq:Reset} \begin{array}{l} \overline{\text{Reset}} \text{ to Q or } \overline{\text{Q}} \\ \text{t}_{\text{PLH}}, \text{t}_{\text{PHL}} = (0.90 \text{ ns/pF}) \text{ C}_{\text{L}} + 205 \text{ ns} \\ \text{t}_{\text{PLH}}, \text{t}_{\text{PHL}} = (0.36 \text{ ns/pF}) \text{ C}_{\text{L}} + 107 \text{ ns} \\ \text{t}_{\text{PLH}}, \text{t}_{\text{PHL}} = (0.26 \text{ ns/pF}) \text{ C}_{\text{L}} + 82 \text{ ns} \end{array}$		5.0 10 15	- - -	250 125 95	500 250 190	ns
Input Rise and Fall Times Reset	t _r , t _f	5 10 15	- - -	- - -	15 5 4	μs
B Input		5 10 15	- - -	300 1.2 0.4	1.0 0.1 0.05	ms
A Input		5 10 15		No Limit	,	-
Input Pulse Width A, B, or Reset	t _{WH} , t _{WL}	5.0 10 15	170 90 80	85 45 40	- - -	ns
Retrigger Time	t _{rr}	5.0 10 15	0 0 0	- - -	- - -	ns
Output Pulse Width — Q or \overline{Q} Refer to Figures 8 and 9	Т					μs
C_X = 0.002 μ F, R_X = 100 $k\Omega$		5.0 10 15	198 200 202	210 212 214	230 232 234	
C_X = 0.1 μ F, R_X = 100 $k\Omega$		5.0 10 15	9.3 9.4 9.5	9.86 10 10.14	10.5 10.6 10.7	ms
C_X = 10 μ F, R_X = 100 $k\Omega$		5.0 10 15	0.91 0.92 0.93	0.965 0.98 0.99	1.03 1.04 1.06	S
Pulse Width Match between circuits in the same package. $C_X = 0.1 \mu \text{F}, R_X = 100 \text{k}\Omega$	100 [(T ₁ - T ₂)/T ₁]	5.0 10 15	- - -	±1.0 ±1.0 ±1.0	±5.0 ±5.0 ±5.0	%

^{6.} The formulas given are for the typical characteristics only at 25°C.
7. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

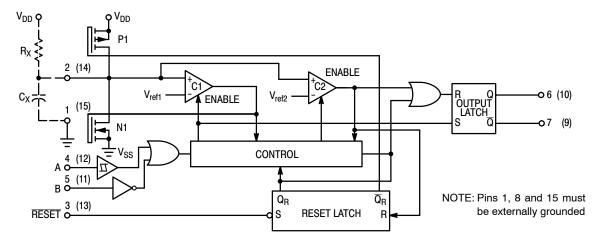


Figure 1. Logic Diagram (1/2 of Device Shown)

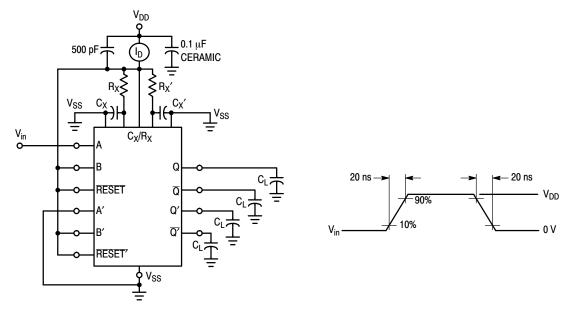


Figure 2. Power Dissipation Test Circuit and Waveforms

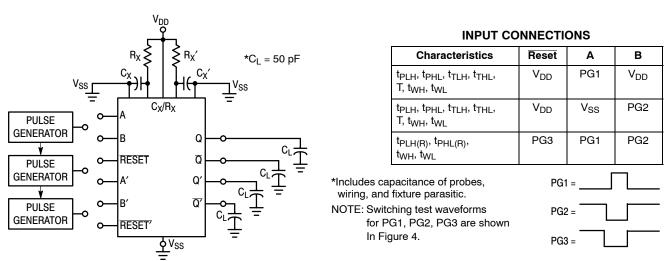


Figure 3. Switching Test Circuit

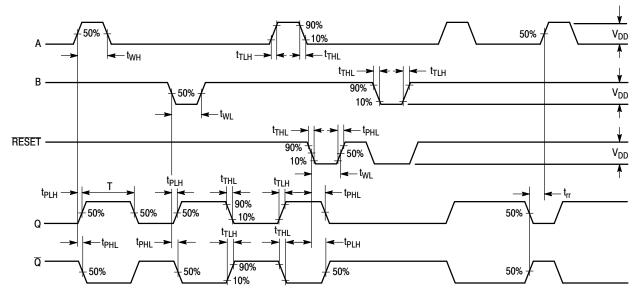


Figure 4. Switching Test Waveforms

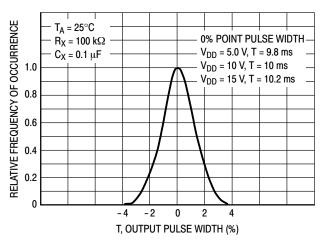


Figure 5. Typical Normalized Distribution of Units for Output Pulse Width

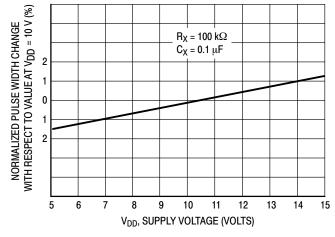


Figure 6. Typical Pulse Width Variation as a Function of Supply Voltage V_{DD}

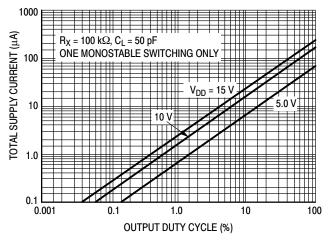


Figure 7. Typical Total Supply Current versus Output Duty Cycle

FUNCTION TABLE

	Inputs	Outputs			
Reset	Α	В	Q	Q	
Н	5	Н	Л	T	
Н	L	7	九	7.	
Н		L	Not Triggered		
Н	Н	∠ _	Not Tr	iggered	
Н	L, H, ∕_	Н	Not Tr	iggered	
Н	L	L, H, 🗸	Not Triggered		
L	Х	Х	L	Н	
~	X	X	Not Tr	iggered	

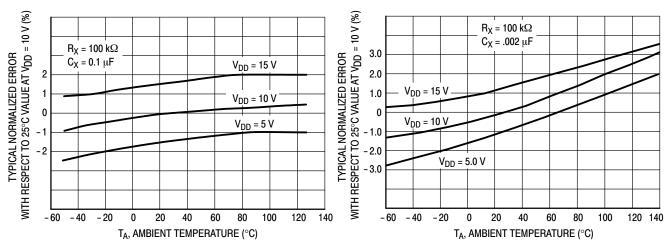


Figure 8. Typical Error of Pulse Width Equation versus Temperature

Figure 9. Typical Error of Pulse Width Equation versus Temperature

THEORY OF OPERATION

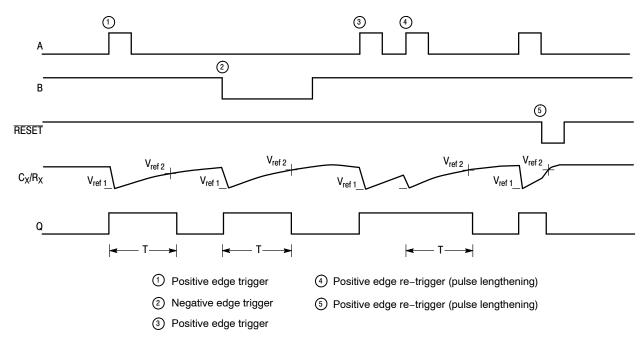


Figure 10. Timing Operation

TRIGGER OPERATION

The block diagram of the MC14538B is shown in Figure 1, with circuit operation following.

As shown in Figure 1 and 10, before an input trigger occurs, the monostable is in the quiescent state with the Q output low, and the timing capacitor C_X completely charged to V_{DD} . When the trigger input A goes from V_{SS} to V_{DD} (while inputs B and $\overline{\text{Reset}}$ are held to V_{DD}) a valid trigger is recognized, which turns on comparator C1 and N-channel transistor N1 1. At the same time the output latch is set. With transistor N1 on, the capacitor C_X rapidly discharges toward V_{SS} until V_{ref1} is reached. At this point the output of comparator C1 changes state and transistor N1 turns off. Comparator C1 then turns off while at the same time comparator C2 turns on. With transistor N1 off, the capacitor C_X begins to charge through the timing resistor, R_X , toward V_{DD} . When the voltage across C_X equals $V_{ref 2}$, comparator C2 changes state, causing the output latch to reset (Q goes low) while at the same time disabling comparator C2 2. This ends at the timing cycle with the monostable in the quiescent state, waiting for the next trigger.

In the quiescent state, C_X is fully charged to V_{DD} causing the current through resistor R_X to be zero. Both comparators are "off" with total device current due only to reverse junction leakages. An added feature of the MC14538B is that the output latch is set via the input trigger without regard to the capacitor voltage. Thus, propagation delay from trigger to Q is independent of the value of C_X , R_X , or the duty cycle of the input waveform.

RETRIGGER OPERATION

RESET OPERATION

The MC14538B may be reset during the generation of the output pulse. In the reset mode of operation, an input pulse

on \overline{Reset} sets the reset latch and causes the capacitor to be fast charged to V_{DD} by turning on transistor P1 $\footnote{\circ}$. When the voltage on the capacitor reaches $V_{ref~2}$, the reset latch will clear, and will then be ready to accept another pulse. It the \overline{Reset} input is held low, any trigger inputs that occur will be inhibited and the Q and \overline{Q} outputs of the output latch will not change. Since the Q output is reset when an input low level is detected on the \overline{Reset} input, the output pulse T can be made significantly shorter than the minimum pulse width specification.

POWER-DOWN CONSIDERATIONS

Large capacitance values can cause problems due to the large amount of energy stored. When a system containing the MC14538B is powered down, the capacitor voltage may discharge from V_{DD} through the standard protection diodes at pin 2 or 14. Current through the protection diodes should be limited to 10 mA and therefore the discharge time of the V_{DD} supply must not be faster than (V_{DD}) . (C)/(10 mA). For example, if V_{DD} = 10 V and C_X = 10 μF , the V_{DD} supply should discharge no faster than (10 V) x (10 μF)/(10 mA) = 10 ms. This is normally not a problem since power supplies are heavily filtered and cannot discharge at this rate.

When a more rapid decrease of V_{DD} to zero volts occurs, the MC14538B can sustain damage. To avoid this possibility use an external clamping diode, D_X , connected as shown in Fig. 11.

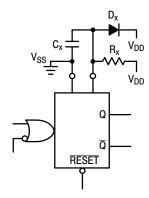
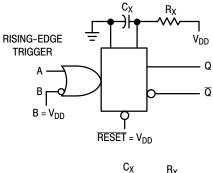


Figure 11. Use of a Diode to Limit Power Down Current Surge

TYPICAL APPLICATIONS



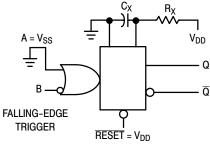


Figure 12. Retriggerable Monostables Circuitry

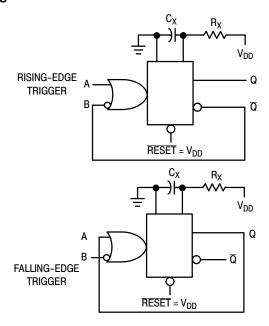


Figure 13. Non-Retriggerable Monostables Circuitry

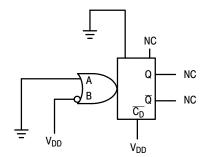
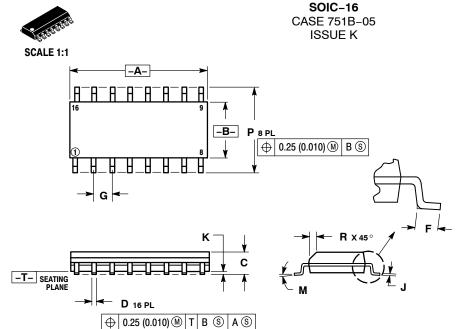


Figure 14. Connection of Unused Sections



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.		PIN 1.		PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	#1	
2.			ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR			8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE		CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.		11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER		CATHODE	12.		12.			
13.	BASE		CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	SOI DEDING	FOOTPRINT
14.			NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	FOOTFRINT
15.	EMITTER		ANODE	15.	EMITTER, #4	15.	BASE, #1	8	ЗX
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	- 6	.40 ────
								-	-
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12 <
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				,
2.	DRAIN. #1		CATHODE	2.	COMMON DRAIN (OUTPUT)		. 🗀 1	16
3.	DRAIN, #2		CATHODE	3.	COMMON DRAIN (OUTPUT			,	'' 🖳
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	,			
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT)	16	5X T	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT		0.5		' <u> </u>
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPUT		0.0		
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT				
13.	GATE, #2	13.	ANODE	13.	GATE N-CH	,			¦
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT)			▼ PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT				<u>+-+</u>
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH	,			
	- /							□ 8	9 + - + -
								•	,
									BINENIOLONIO MILLINETTE
									DIMENSIONS: MILLIMETERS

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DESCRIPTION:	SOIC-16		PAGE 1 OF 1	

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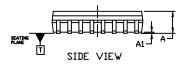


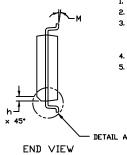




DATE 08 OCT 2021

SCALE 1:1 **♦** 0.25**₩** B**₩** RRRR PIN 1 --INDICATOR -16X R **♦** 0.25**®** TAS BS TOP VIEW





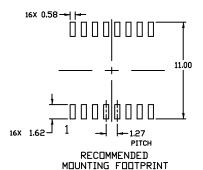


DETAIL A

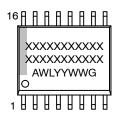
NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- MAXIMUM MOLD PROTRUSION OR FLASH TO BE 0.15 PER SIDE.

	MILLIMETERS			
DIM	MIN.	MAX.		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	10.15	10.45		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.53 REF			
١	0.50	0.90		
М	0*	7*		



GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot YY = Year ww = Work Week = Pb-Free Package

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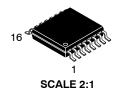
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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

0.10 (0.004)

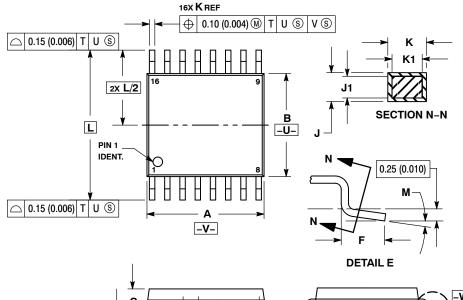
D

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



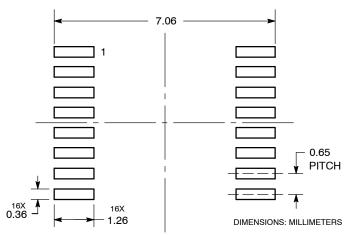
NOTES

- JIES:
 DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	6.40 BSC		BSC	
М	0 °	8 °	0 °	8 °	



G



GENERIC MARKING DIAGRAM*

168888888 XXXX XXXX **ALYW** 188888888

XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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